

Ultra Low ON-Resistance, +1.65V to +4.5V, Single Supply, Dual SPDT Analog Switch

The Intersil ISL8484 device is a low ON-resistance, low voltage, bidirectional, dual single-pole/double-throw (SPDT) analog switch designed to operate from a single +1.65V to +4.5V supply. Targeted applications include battery powered equipment that benefit from low R_{ON} (0.23Ω) and fast switching speeds ($t_{ON} = 20ns$, $t_{OFF} = 15ns$). The digital logic input is 1.8V logic-compatible when using a single +3V supply.

With a supply voltage of 4.2V and logic high voltage of 2.85V at both logic inputs, the part draws only 10 μ A max of I+ current.

Cell phones, for example, often face ASIC functionality limitations. The number of analog input or GPIO pins may be limited and digital geometries are not well suited to analog switch performance. This part may be used to “mux-in” additional functionality while reducing ASIC design risk. The ISL8484 is offered in small form factor packages, alleviating board space limitations.

The ISL8484 is a committed dual single-pole/double-throw (SPDT) that consist of two normally open (NO) and two normally closed (NC) switches. This configuration can be used as a dual 2-to-1 multiplexer. The ISL8484 is pin compatible with the MAX4684 and MAX4685.

TABLE 1. FEATURES AT A GLANCE

	ISL8484
Number of Switches	2
SW	SPDT or 2-1 MUX
4.3V R_{ON}	0.23Ω
4.3V t_{ON}/t_{OFF}	20ns/15ns
3V R_{ON}	0.27Ω
3V t_{ON}/t_{OFF}	25ns/20ns
1.8V R_{ON}	0.45Ω
1.8V t_{ON}/t_{OFF}	65ns/50ns
Packages	10 Ld 3x3 Thin DFN, 10 Ld MSOP

Related Literature

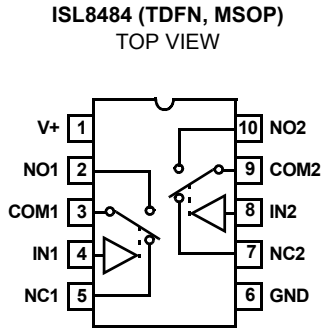
- Technical Brief TB363 “Guidelines for Handling and Processing Moisture Sensitive Surface Mount Devices (SMDs)”
- Application Note AN557 “Recommended Test Procedures for Analog Switches”

Features

- Pb-Free Available as an Option (RoHS Compliant) (see Ordering Info)
- Pin Compatible Replacement for the MAX4684 and MAX4685
- ON Resistance (R_{ON})
 - $V+ = +4.3V$ 0.23Ω
 - $V+ = +3.0V$ 0.27Ω
 - $V+ = +1.8V$ 0.45Ω
- R_{ON} Matching Between Channels 0.03Ω
- R_{ON} Flatness Across Signal Range 0.03Ω
- Single Supply Operation +1.65V to +4.5V
- Low Power Consumption (P_D) <0.3 μ W
- Fast Switching Action ($V+ = +4.3V$)
 - t_{ON} 20ns
 - t_{OFF} 15ns
- ESD HBM Rating >9kV
- Guaranteed Break-before-Make
- 1.8V Logic Compatible (+3V supply)
- Low I+ Current when VinH is not at the V+ Rail
- Available in 10 lead 3x3 Thin DFN and 10 lead MSOP

Applications

- Battery powered, Handheld, and Portable Equipment
 - Cellular/mobile Phones
 - Pagers
 - Laptops, Notebooks, Palmtops
- Portable Test and Measurement
- Medical Equipment
- Audio and Video Switching

Pinout (Note 1)

NOTE:

1. Switches Shown for Logic "0" Input.

Truth Table

LOGIC	PIN NC1 and NC2	PIN NO1 and NO2
0	ON	OFF
1	OFF	ON

NOTE: Logic "0" $\leq 0.5V$. Logic "1" $\geq 1.4V$ with a 3V supply.**Pin Descriptions**

PIN	FUNCTION
V+	System Power Supply Input (+1.65V to +4.5V)
GND	Ground Connection
IN	Digital Control Input
COM	Analog Switch Common Pin
NO	Analog Switch Normally Open Pin
NC	Analog Switch Normally Closed Pin

Ordering Information

PART NO. (BRAND)	TEMP. RANGE (°C)	PACKAGE	PKG. DWG. #
ISL8484IR (484)	-40 to 85	10 Ld 3x3 Thin DFN	L10.3x3A
ISL8484IR-T (484)	-40 to 85	10 Ld 3x3 Thin DFN Tape and Reel	L10.3x3A
ISL8484IU (8484)	-40 to 85	10 Ld MSOP	M10.118
ISL8484IU-T (8484)	-40 to 85	10 Ld MSOP Tape and Reel	M10.118
ISL8484IRZ (484Z) (See Note)	-40 to 85	10 Ld 3x3 Thin DFN (Pb-free)	L10.3x3A
ISL8484IRZ-T (484Z) (See Note)	-40 to 85	10 Ld 3x3 Thin DFN Tape and Reel (Pb-free)	L10.3x3A
ISL8484IUZ (8484Z) (See Note)	-40 to 85	10 Ld MSOP (Pb-free)	M10.118
ISL8484IUZ-T (8484Z) (See Note)	-40 to 85	10 Ld MSOP Tape and Reel (Pb-free)	M10.118

NOTE: Intersil Pb-free products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

Absolute Maximum Ratings

V+ to GND	-0.3 to 4.7V
Input Voltages	
NO, NC, IN (Note 2)	-0.3 to ((V+) + 0.3V)
Output Voltages	
COM (Note 2)	-0.3 to ((V+) + 0.3V)
Continuous Current NO, NC, or COM	±300mA
Peak Current NO, NC, or COM (Pulsed 1ms, 10% Duty Cycle, Max)	±500mA
ESD Rating:	
HBM	>9kV
MM	>500V
CDM	>1kV

Thermal Information

Thermal Resistance (Typical)	θ_{JA} (°C/W)
10 Ld 3x3 TDFN Package (Note 3)	110
10 Ld MSOP Package (Note 3)	190
Maximum Junction Temperature (Plastic Package)	150°C
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s) (Lead Tips Only)	300°C

Operating Conditions

Temperature Range	
ISL8484IX	-40°C to 85°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTES:

- Signals on NC, NO, IN, or COM exceeding V+ or GND are clamped by internal diodes. Limit forward diode current to maximum current ratings.
- θ_{JA} is measured with the component mounted on a low effective thermal conductivity test board in free air. See Tech Brief TB379 for details.

Electrical Specifications - 4.3V Supply

Test Conditions: V+ = +3.9V to +4.5V, GND = 0V, V_{INH} = 1.6V, V_{INL} = 0.5V (Notes 4, 6), Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	TYP	(NOTE 5) MAX	UNITS
ANALOG SWITCH CHARACTERISTICS						
Analog Signal Range, V _{ANALOG}		Full	0	-	V+	V
ON Resistance, R _{ON}	V+ = 3.9V, I _{COM} = 100mA, V _{NO} or V _{NC} = 0V to V+, (See Figure 5)	25	-	0.23	-	Ω
		Full	-	0.26	-	Ω
R _{ON} Matching Between Channels, ΔR _{ON}	V+ = 3.9V, I _{COM} = 100mA, V _{NO} or V _{NC} = Voltage at max R _{ON} , (Note 9)	25	-	0.03	-	Ω
		Full	-	0.04	-	Ω
R _{ON} Flatness, R _{FLAT(ON)}	V+ = 3.9V, I _{COM} = 100mA, V _{NO} or V _{NC} = 0V to V+, (Note 7)	25	-	0.03	-	Ω
		Full	-	0.04	-	Ω
NO or NC OFF Leakage Current, I _{NO(OFF)} or I _{NC(OFF)}	V+ = 4.5V, V _{COM} = 0.3V, 3V, V _{NO} or V _{NC} = 3V, 0.3V	25	-45	-	45	nA
		Full	-110	-	110	nA
COM ON Leakage Current, I _{COM(ON)}	V+ = 4.5V, V _{COM} = 0.3V, 3V, or V _{NO} or V _{NC} = 0.3V, 3V, or Floating	25	-45	-	45	nA
		Full	-100	-	100	nA
DYNAMIC CHARACTERISTICS						
Turn-ON Time, t _{ON}	V+ = 3.9V, V _{NO} or V _{NC} = 3.0V, R _L = 50Ω, C _L = 35pF, (See Figure 1, Note 8)	25	-	20	30	ns
		Full	-	-	35	ns
Turn-OFF Time, t _{OFF}	V+ = 3.9V, V _{NO} or V _{NC} = 3.0V, R _L = 50Ω, C _L = 35pF, (See Figure 1, Note 8)	25	-	15	25	ns
		Full	-	-	30	ns
Break-Before-Make Time Delay, t _D	V+ = 4.5V, V _{NO} or V _{NC} = 3.0V, R _L = 50Ω, C _L = 35pF, (See Figure 3, Note 8)	Full	2	4	-	ns
Charge Injection, Q	C _L = 1.0nF, V _G = 0V, R _G = 0Ω, (See Figure 2)	25	-	128	-	pC
OFF Isolation	R _L = 50Ω, C _L = 5pF, f = 100kHz, V _{COM} = 1V _{RMS} , (See Figure 4)	25	-	68	-	dB
Crosstalk (Channel-to-Channel)	R _L = 50Ω, C _L = 5pF, f = 100kHz, V _{COM} = 1V _{RMS} , (See Figure 6)	25	-	-95	-	dB
Total Harmonic Distortion	f = 20Hz to 20kHz, V _{COM} = 2V _{P-P} , R _L = 600Ω	25	-	0.003	-	%
NO or NC OFF Capacitance, C _{OFF}	f = 1MHz, V _{NO} or V _{NC} = V _{COM} = 0V, (See Figure 7)	25	-	115	-	pF

Electrical Specifications - 4.3V Supply

Test Conditions: $V_+ = +3.9V$ to $+4.5V$, $GND = 0V$, $V_{INH} = 1.6V$, $V_{INL} = 0.5V$ (Notes 4, 6),
Unless Otherwise Specified **(Continued)**

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	TYP	(NOTE 5) MAX	UNITS
COM ON Capacitance, $C_{COM(ON)}$	$f = 1MHz$, V_{NO} or $V_{NC} = V_{COM} = 0V$, (See Figure 7)	25	-	224	-	pF
POWER SUPPLY CHARACTERISTICS						
Power Supply Range		Full	1.65		4.5	V
Positive Supply Current, I_+	$V_+ = +4.5V$, $V_{IN} = 0V$ or V_+	25	-	-	0.08	μA
		Full	-	-	1	μA
Positive Supply Current, I_+	$V_+ = +4.2V$, $V_{IN} = 2.85V$	25	-	-	10	μA
DIGITAL INPUT CHARACTERISTICS						
Input Voltage Low, V_{INL}		Full	-	-	0.5	V
Input Voltage High, V_{INH}		Full	1.6	-	-	V
Input Current, I_{INH} , I_{INL}	$V_+ = 4.5V$, $V_{IN} = 0V$ or V_+ , (Note 8)	Full	-0.5	-	0.5	μA

NOTES:

- V_{IN} = input voltage to perform proper function.
- The algebraic convention, whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Parts are 100% tested at $+25^\circ C$. Limits across the full temperature range are guaranteed by design and correlation.
- Flatness is defined as the difference between maximum and minimum value of on-resistance over the specified analog signal range.
- Guaranteed but not tested.
- R_{ON} matching between channels is calculated by subtracting the channel with the highest max Ron value from the channel with lowest max Ron value, between NC1 and NC2 or between NO1 and NO2.

Electrical Specifications - 3V Supply

Test Conditions: $V_+ = +2.7V$ to $+3.3V$, $GND = 0V$, $V_{INH} = 1.4V$, $V_{INL} = 0.5V$ (Notes 4, 6),
Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	TYP	(NOTE 5) MAX	UNITS
ANALOG SWITCH CHARACTERISTICS						
Analog Signal Range, V_{ANALOG}		Full	0	-	V+	V
ON Resistance, R_{ON}	$V+ = 2.7V$, $I_{COM} = 100mA$, V_{NO} or $V_{NC} = 0V$ to $V+$, (See Figure 5)	25	-	0.29	0.4	Ω
		Full	-	-	0.6	Ω
R_{ON} Matching Between Channels, ΔR_{ON}	$V+ = 2.7V$, $I_{COM} = 100mA$, V_{NO} or $V_{NC} =$ Voltage at max R_{ON} , (Note 9)	25	-	0.03	0.06	Ω
		Full	-	-	0.06	Ω
R_{ON} Flatness, $R_{FLAT(ON)}$	$V+ = 2.7V$, $I_{COM} = 100mA$, V_{NO} or $V_{NC} = 0V$ to $V+$, (Note 7)	25	-	0.03	0.15	Ω
		Full	-	-	0.15	Ω
NO or NC OFF Leakage Current, $I_{NO(OFF)}$ or $I_{NC(OFF)}$	$V+ = 3.3V$, $V_{COM} = 0.3V$, $3V$, V_{NO} or $V_{NC} = 3V$, $0.3V$	25	-	1.1	-	nA
		Full	-	25	-	nA
COM ON Leakage Current, $I_{COM(ON)}$	$V+ = 3.3V$, $V_{COM} = 0.3V$, $3V$, or V_{NO} or $V_{NC} = 0.3V$, $3V$, or Floating	25	-	1.7	-	nA
		Full	-	48	-	nA
DYNAMIC CHARACTERISTICS						
Turn-ON Time, t_{ON}	$V+ = 2.7V$, V_{NO} or $V_{NC} = 1.5V$, $R_L = 50\Omega$, $C_L = 35pF$, (See Figure 1, Note 8)	25	-	25	35	ns
		Full	-	-	40	ns
Turn-OFF Time, t_{OFF}	$V+ = 2.7V$, V_{NO} or $V_{NC} = 1.5V$, $R_L = 50\Omega$, $C_L = 35pF$, (See Figure 1, Note 8)	25	-	20	30	ns
		Full	-	-	35	ns
Break-Before-Make Time Delay, t_D	$V+ = 3.3V$, V_{NO} or $V_{NC} = 1.5V$, $R_L = 50\Omega$, $C_L = 35pF$, (See Figure 3, Note 8)	Full	2	6	-	ns

Electrical Specifications - 3V Supply

Test Conditions: $V_+ = +2.7V$ to $+3.3V$, $GND = 0V$, $V_{INH} = 1.4V$, $V_{INL} = 0.5V$ (Notes 4, 6), Unless Otherwise Specified **(Continued)**

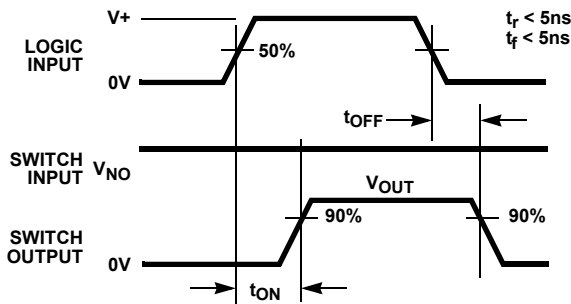
PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	TYP	(NOTE 5) MAX	UNITS
Charge Injection, Q	C _L = 1.0nF, V _G = 0V, R _G = 0Ω, (See Figure 2)	25	-	95	-	pC
OFF Isolation	R _L = 50Ω, C _L = 5pF, f = 100kHz, V _{COM} = 1V _{RMS} , (See Figure 4)	25	-	68	-	dB
Crosstalk (Channel-to-Channel)	R _L = 50Ω, C _L = 5pF, f = 100kHz, V _{COM} = 1V _{RMS} , (See Figure 6)	25	-	-95	-	dB
Total Harmonic Distortion	f = 20Hz to 20kHz, V _{COM} = 2V _{P-P} , R _L = 600Ω	25	-	0.003	-	%
NO or NC OFF Capacitance, C _{OFF}	f = 1MHz, V _{NO} or V _{NC} = V _{COM} = 0V, (See Figure 7)	25	-	115	-	pF
COM ON Capacitance, C _{COM(ON)}	f = 1MHz, V _{NO} or V _{NC} = V _{COM} = 0V, (See Figure 7)	25	-	224	-	pF
POWER SUPPLY CHARACTERISTICS						
Positive Supply Current, I+	V+ = +3.6V, V _{IN} = 0V or V+	25	-	0.014	-	μA
		Full	-	0.52	-	μA
DIGITAL INPUT CHARACTERISTICS						
Input Voltage Low, V _{INL}		25	-	-	0.5	V
Input Voltage High, V _{INH}		25	1.4	-	-	V
Input Current, I _{INH} , I _{INL}	V+ = 3.3V, V _{IN} = 0V or V+ (Note 8)	Full	-0.5	-	0.5	μA

Electrical Specifications - 1.8V Supply

Test Conditions: $V_+ = +1.65V$ to $+2V$, $GND = 0V$, $V_{INH} = 1.0V$, $V_{INL} = 0.4V$ (Note 4, 6), Unless Otherwise Specified

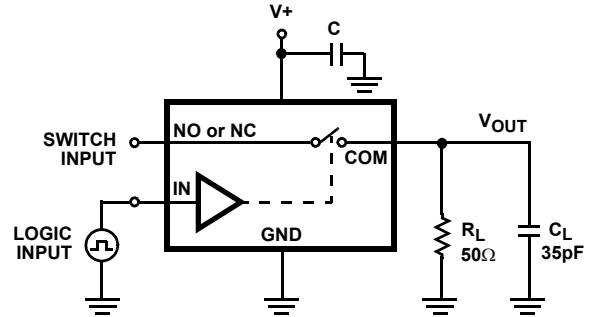
PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	TYP	(NOTE 5) MAX	UNITS
ANALOG SWITCH CHARACTERISTICS						
Analog Signal Range, V _{ANALOG}		Full	0	-	V+	V
ON Resistance, R _{ON}	V+ = 1.65V, I _{COM} = 100mA, V _{NO} or V _{NC} = 0V to V+, (See Figure 5)	25	-	0.5	0.8	Ω
		Full	-	-	0.85	Ω
DYNAMIC CHARACTERISTICS						
Turn-ON Time, t _{ON}	V+ = 1.65V, V _{NO} or V _{NC} = 1.0V, R _L = 50Ω, C _L = 35pF, (See Figure 1, Note 8)	25	-	65	80	ns
		Full	-	-	90	ns
Turn-OFF Time, t _{OFF}	V+ = 1.65V, V _{NO} or V _{NC} = 1.0V, R _L = 50Ω, C _L = 35pF, (See Figure 1, Note 8)	25	-	50	70	ns
		Full	-	-	80	ns
Break-Before-Make Time Delay, t _D	V+ = 2.0V, V _{NO} or V _{NC} = 1.0V, R _L = 50Ω, C _L = 35pF, (See Figure 3, Note 8)	Full	2	9	-	ns
Charge Injection, Q	C _L = 1.0nF, V _G = 0V, R _G = 0Ω, (See Figure 2)	25	-	49	-	pC
OFF Isolation	R _L = 50Ω, C _L = 5pF, f = 100kHz, V _{COM} = 1V _{RMS} . (See Figure 4)	25	-	68	-	dB
Crosstalk (Channel-to-Channel)	R _L = 50Ω, C _L = 5pF, f = 100kHz, V _{COM} = 1V _{RMS} . (See Figure 6)	25	-	-95	-	dB
NO or NC OFF Capacitance, C _{OFF}	f = 1MHz, V _{NO} or V _{NC} = V _{COM} = 0V, (See Figure 7)	25	-	115	-	pF
COM ON Capacitance, C _{COM(ON)}	f = 1MHz, V _{NO} or V _{NC} = V _{COM} = 0V, (See Figure 7)	25	-	224	-	pF
DIGITAL INPUT CHARACTERISTICS						
Input Voltage Low, V _{INL}		25	-	-	0.4	V
Input Voltage High, V _{INH}		25	1.0	-	-	V
Input Current, I _{INH} , I _{INL}	V+ = 2.0V, V _{IN} = 0V or V+ (Note 8)	Full	-0.5	-	0.5	μA

Test Circuits and Waveforms



Logic input waveform is inverted for switches that have the opposite logic sense.

FIGURE 1A. MEASUREMENT POINTS



Repeat test for all switches. C_L includes fixture and stray capacitance.

$$V_{OUT} = V_{(NO \text{ or } NC)} \frac{R_L}{R_L + R_{(ON)}}$$

FIGURE 1B. TEST CIRCUIT

FIGURE 1. SWITCHING TIMES

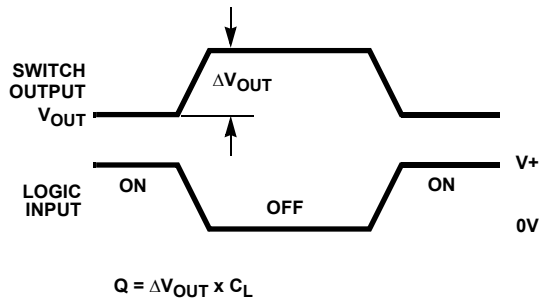
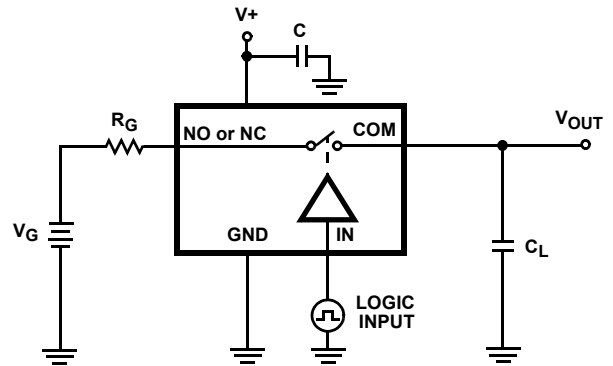


FIGURE 2A. MEASUREMENT POINTS



Repeat test for all switches.

FIGURE 2B. TEST CIRCUIT

FIGURE 2. CHARGE INJECTION

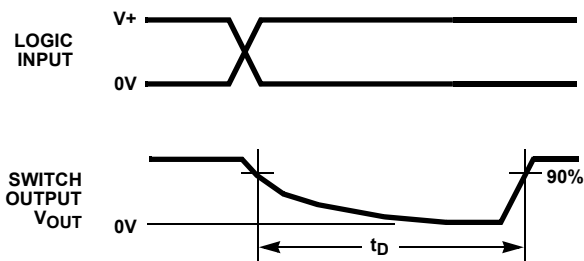
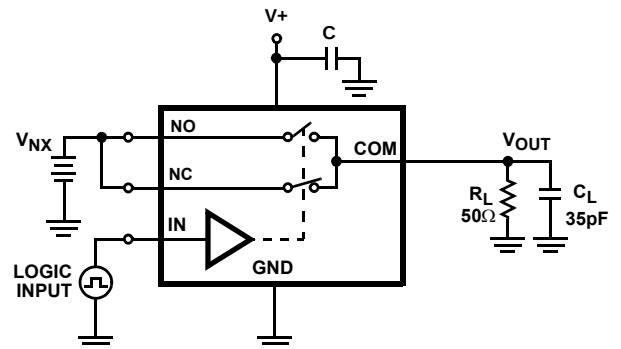


FIGURE 3A. MEASUREMENT POINTS

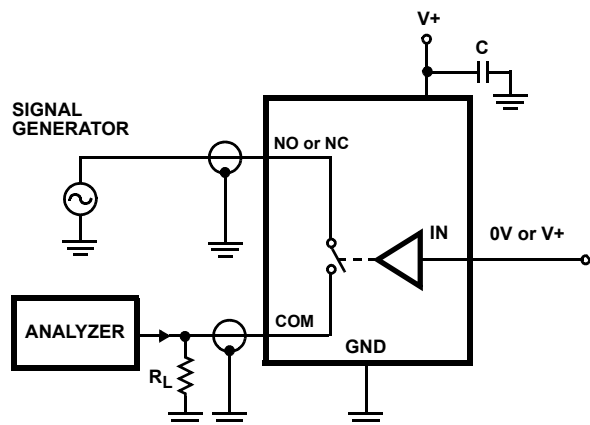


Repeat test for all switches. C_L includes fixture and stray capacitance.

FIGURE 3B. TEST CIRCUIT

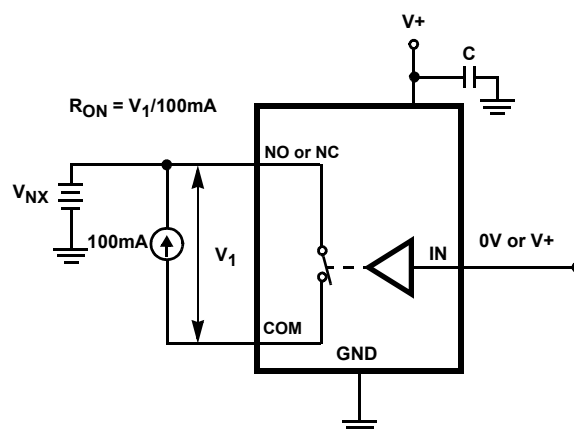
FIGURE 3. BREAK-BEFORE-MAKE TIME

Test Circuits and Waveforms (Continued)



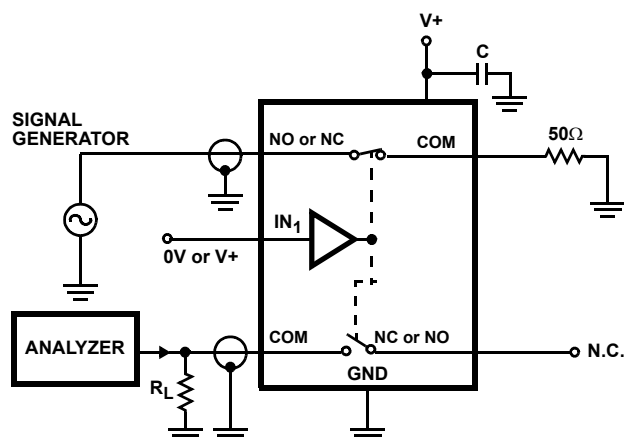
Signal direction through switch is reversed, worst case values are recorded. Repeat test for all switches.

FIGURE 4. OFF ISOLATION TEST CIRCUIT



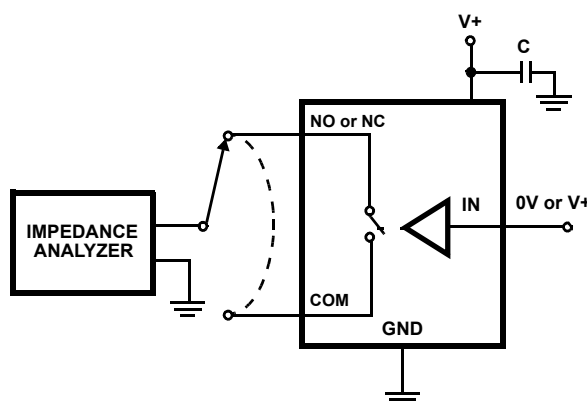
Repeat test for all switches.

FIGURE 5. R_{ON} TEST CIRCUIT



Signal direction through switch is reversed, worst case values are recorded. Repeat test for all switches.

FIGURE 6. CROSSTALK TEST CIRCUIT



Repeat test for all switches.

FIGURE 7. CAPACITANCE TEST CIRCUIT

Detailed Description

The ISL8484 is a bidirectional, dual single pole/double throw (SPDT) analog switch that offers precise switching capability from a single 1.65V to 4.5V supply with low on-resistance (0.23Ω) and high speed operation ($t_{ON} = 20\text{ns}$, $t_{OFF} = 15\text{ns}$). The device is especially well suited for portable battery powered equipment due to its low operating supply voltage (1.65V), low power consumption ($4.5\mu\text{W}$ max), low leakage currents (110nA max), and the tiny DFN and MSOP packages. The ultra low on-resistance and Ron flatness provide very low insertion loss and distortion to applications that require signal reproduction.

Supply Sequencing and Overvoltage Protection

With any CMOS device, proper power supply sequencing is required to protect the device from excessive input currents which might permanently damage the IC. All I/O pins contain

ESD protection diodes from the pin to V+ and to GND (see Figure 8). To prevent forward biasing these diodes, V+ must be applied before any input signals, and the input signal voltages must remain between V+ and GND. If these conditions cannot be guaranteed, then one of the following two protection methods should be employed.

Logic inputs can easily be protected by adding a $1\text{k}\Omega$ resistor in series with the input (see Figure 8). The resistor limits the input current below the threshold that produces permanent damage, and the sub-microamp input current produces an insignificant voltage drop during normal operation.

This method is not acceptable for the signal path inputs. Adding a series resistor to the switch input defeats the purpose of using a low R_{ON} switch, so two small signal diodes can be added in series with the supply pins to provide

overvoltage protection for all pins (see Figure 8). These additional diodes limit the analog signal from 1V below $V+$ to 1V above GND. The low leakage current performance is unaffected by this approach, but the switch signal range is reduced and the resistance may increase, especially at low supply voltages.

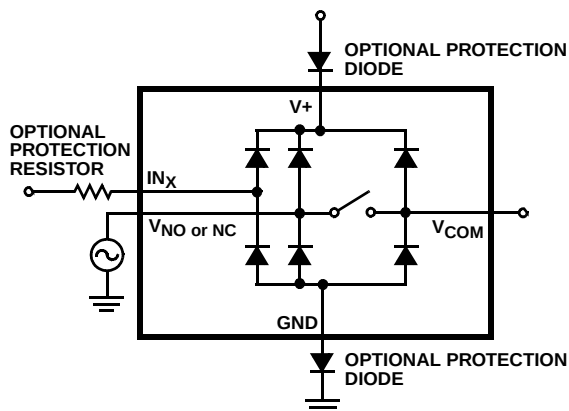


FIGURE 8. OVERVOLTAGE PROTECTION

Power-Supply Considerations

The ISL8484 construction is typical of most single supply CMOS analog switches, in that they have two supply pins: $V+$ and GND. $V+$ and GND drive the internal CMOS switches and set their analog voltage limits. Unlike switches with a 4V maximum supply voltage, the ISL8484 4.7V maximum supply voltage provides plenty of room for the 10% tolerance of 4.3V supplies, as well as room for overshoot and noise spikes.

The minimum recommended supply voltage is 1.65V. It is important to note that the input signal range, switching times, and on-resistance degrade at lower supply voltages. Refer to the electrical specification tables and *Typical Performance* curves for details.

$V+$ and GND also power the internal logic and level shifters. The level shifters convert the input logic levels to switched $V+$ and GND signals to drive the analog switch gate terminals.

This family of switches cannot be operated with bipolar supplies, because the input switching point becomes negative in this configuration.

Logic-Level Thresholds

This switch family is 1.8V CMOS compatible (0.5V and 1.4V) over a supply range of 2.7V to 4.5V (see Figure 16). At 2.7V the V_{IL} level is about 0.53V. This is still above the 1.8V CMOS guaranteed low output maximum level of 0.5V, but noise margin is reduced.

The digital input stages draw supply current whenever the digital input voltage is not at one of the supply rails. Driving

the digital input signals from GND to $V+$ with a fast transition time minimizes power dissipation. The ISL8484 has been designed to minimize the supply current whenever the digital input voltage is not driven to the supply rails (0V to $V+$). For example driving the device with 2.85V logic (0V to 2.85V) while operating with a 4.2V supply the device draws only 8 μ A of current (see Figure 14 for $V_{IN} = 2.85V$).

High-Frequency Performance

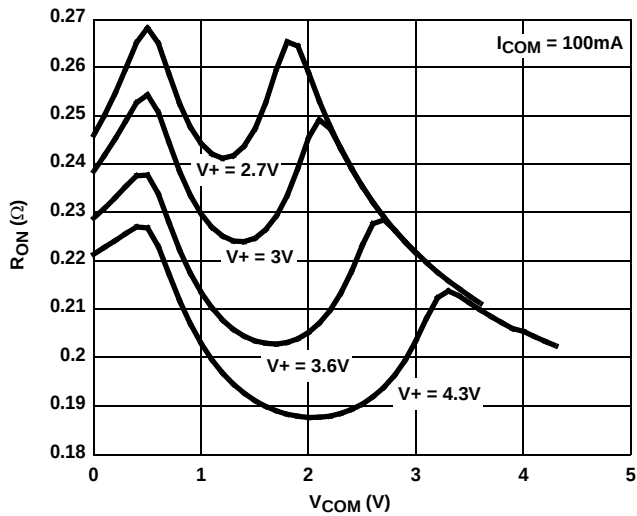
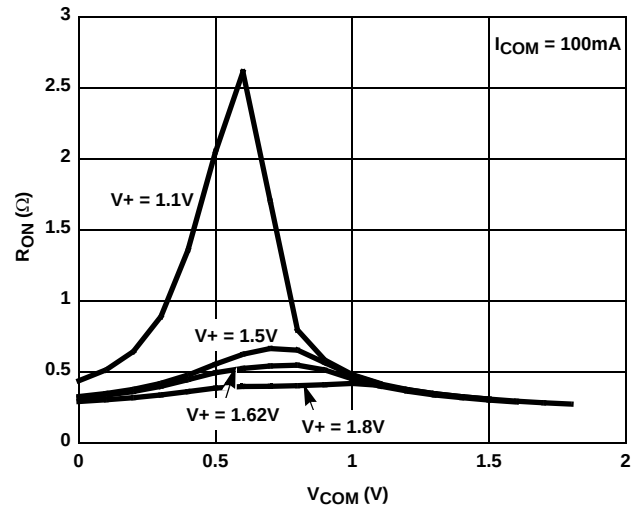
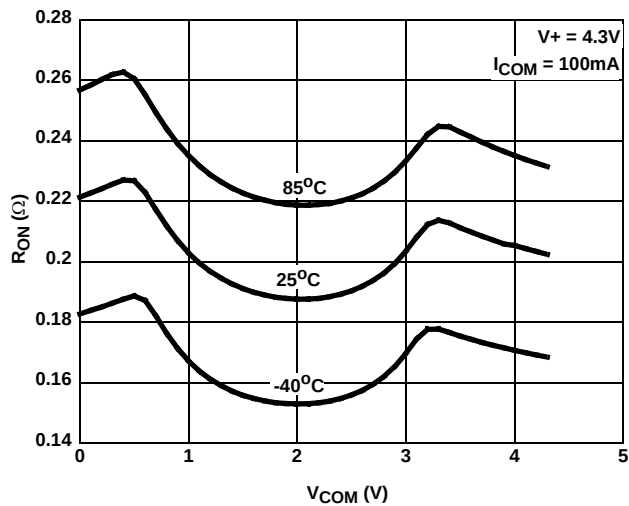
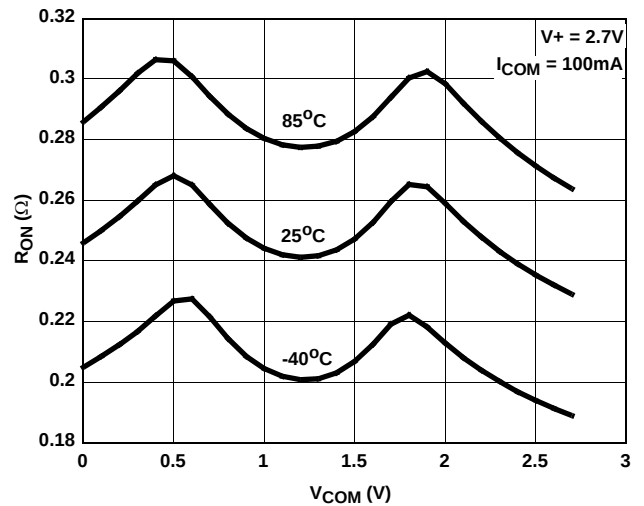
In 50 Ω systems, the signal response is reasonably flat even past 30MHz with a -3dB bandwidth of 120MHz (see Figure 19). The frequency response is very consistent over a wide $V+$ range, and for varying analog signal levels.

An OFF switch acts like a capacitor and passes higher frequencies with less attenuation, resulting in signal feedthrough from a switch's input to its output. Off Isolation is the resistance to this feedthrough, while Crosstalk indicates the amount of feedthrough from one switch to another. Figure 20 details the high Off Isolation and Crosstalk rejection provided by this part. At 100kHz, Off Isolation is about 68dB in 50 Ω systems, decreasing approximately 20dB per decade as frequency increases. Higher load impedances decrease Off Isolation and Crosstalk rejection due to the voltage divider action of the switch OFF impedance and the load impedance.

Leakage Considerations

Reverse ESD protection diodes are internally connected between each analog-signal pin and both $V+$ and GND. One of these diodes conducts if any analog signal exceeds $V+$ or GND.

Virtually all the analog leakage current comes from the ESD diodes to $V+$ or GND. Although the ESD diodes on a given signal pin are identical and therefore fairly well balanced, they are reverse biased differently. Each is biased by either $V+$ or GND and the analog signal. This means their leakages will vary as the signal varies. The difference in the two diode leakages to the $V+$ and GND pins constitutes the analog-signal-path leakage current. All analog leakage current flows between each pin and one of the supply terminals, not to the other switch terminal. This is why both sides of a given switch can show leakage currents of the same or opposite polarity. There is no connection between the analog signal paths and $V+$ or GND.

Typical Performance Curves $T_A = 25^\circ\text{C}$, Unless Otherwise Specified

FIGURE 9. ON RESISTANCE vs SUPPLY VOLTAGE vs SWITCH VOLTAGE

FIGURE 10. ON RESISTANCE vs SUPPLY VOLTAGE vs SWITCH VOLTAGE

FIGURE 11. ON RESISTANCE vs SWITCH VOLTAGE

FIGURE 12. ON RESISTANCE vs SWITCH VOLTAGE

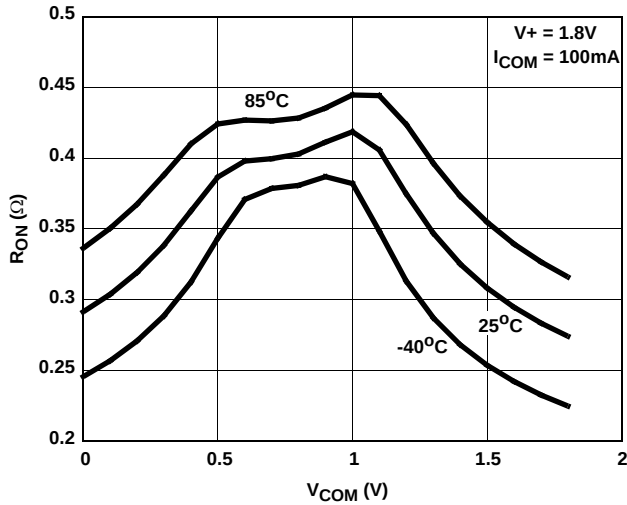
Typical Performance Curves $T_A = 25^\circ\text{C}$, Unless Otherwise Specified (Continued)


FIGURE 13. ON RESISTANCE vs SWITCH VOLTAGE

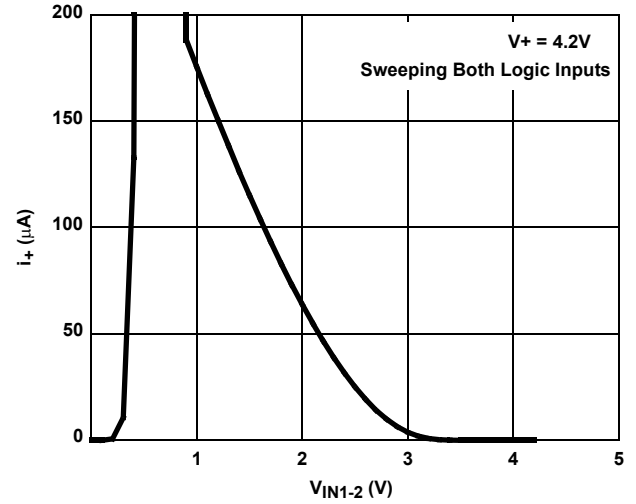


FIGURE 14. VLOGIC vs SUPPLY VOLTAGE

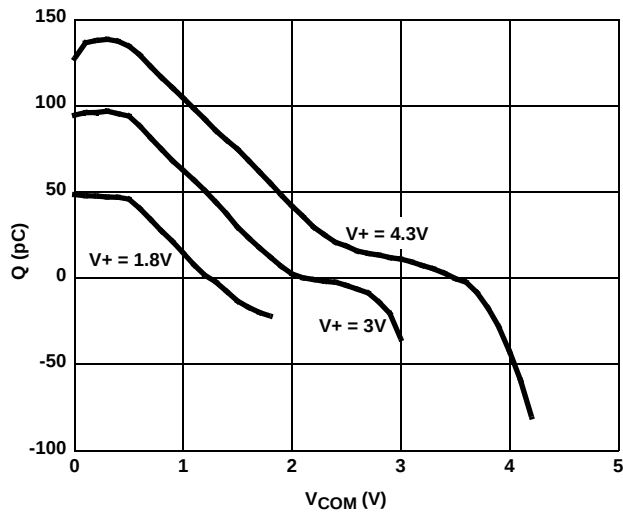


FIGURE 15. CHARGE INJECTION vs SWITCH VOLTAGE

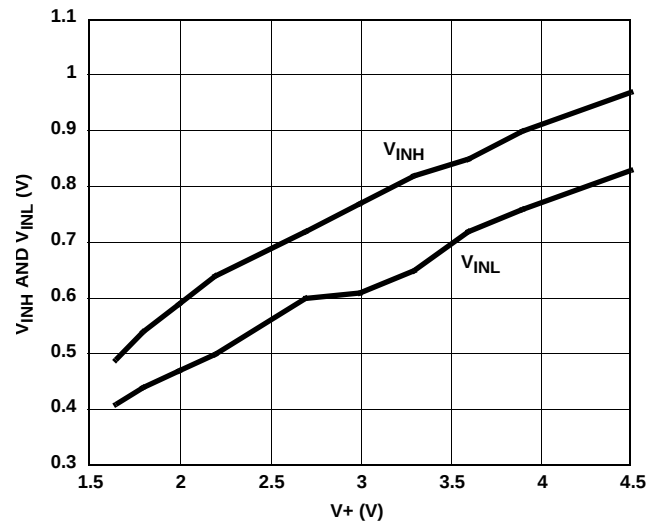


FIGURE 16. DIGITAL SWITCHING POINT vs SUPPLY VOLTAGE

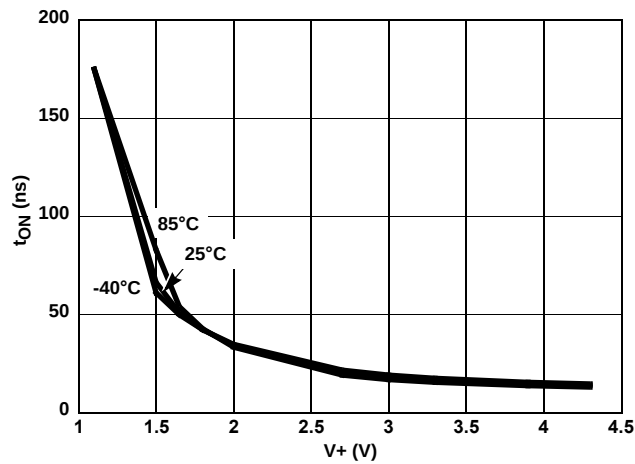


FIGURE 17. TURN - ON TIME vs SUPPLY VOLTAGE

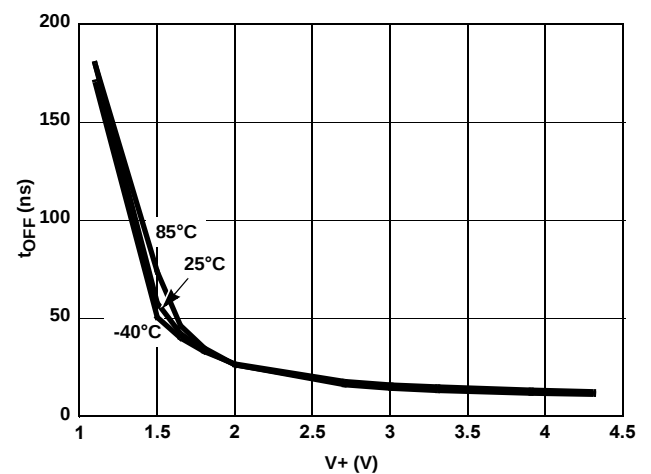


FIGURE 18. TURN - OFF TIME vs SUPPLY VOLTAGE

Typical Performance Curves $T_A = 25^\circ\text{C}$, Unless Otherwise Specified (Continued)

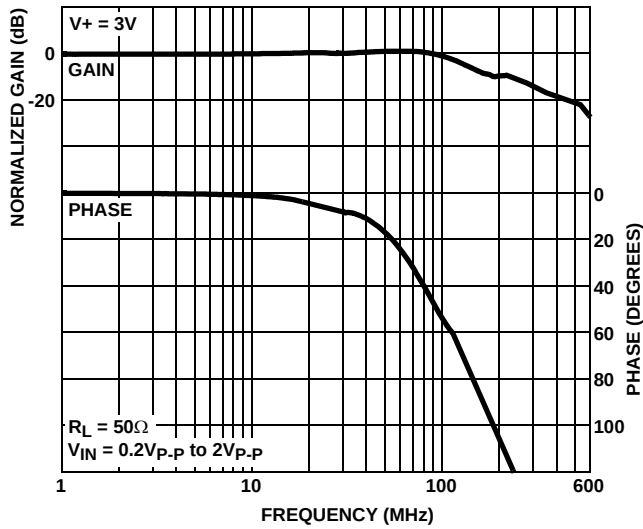


FIGURE 19. FREQUENCY RESPONSE

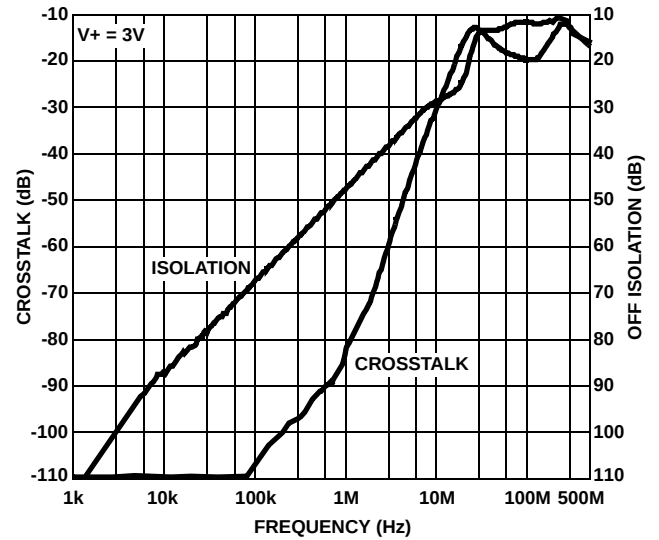


FIGURE 20. CROSSTALK AND OFF ISOLATION

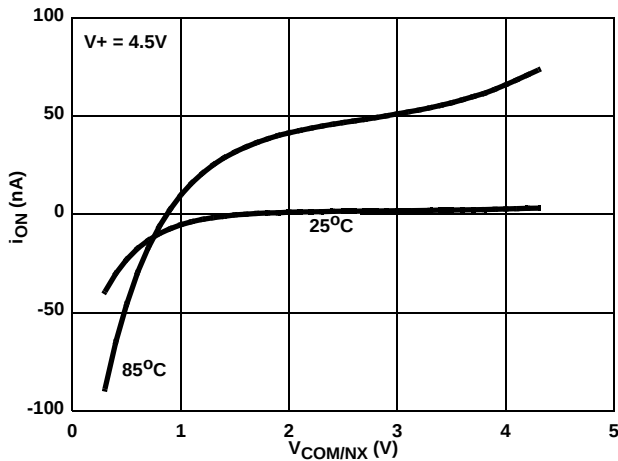


TABLE 2. ON LEAKAGE vs SWITCH VOLTAGE

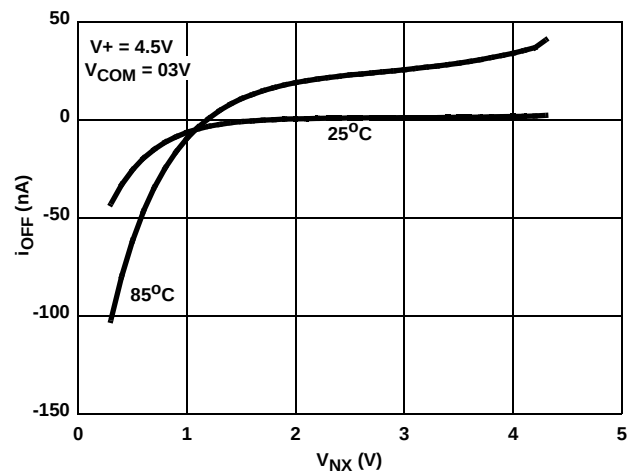


TABLE 3. OFF LEAKAGE vs SWITCH VOLTAGE

Die Characteristics

SUBSTRATE POTENTIAL (POWERED UP):

GND (DFN Paddle Connection: Tie to GND or Float)

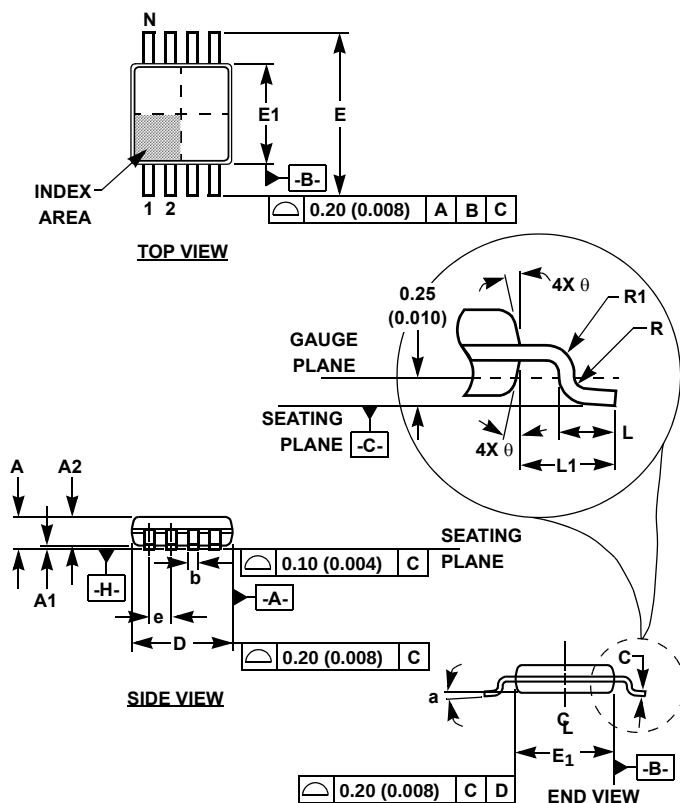
TRANSISTOR COUNT:

114

PROCESS:

Submicron CMOS

Mini Small Outline Plastic Packages (MSOP)



M10.118 (JEDEC MO-187BA)

10 LEAD MINI SMALL OUTLINE PLASTIC PACKAGE

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.037	0.043	0.94	1.10	-
A1	0.002	0.006	0.05	0.15	-
A2	0.030	0.037	0.75	0.95	-
b	0.007	0.011	0.18	0.27	9
c	0.004	0.008	0.09	0.20	-
D	0.116	0.120	2.95	3.05	3
E1	0.116	0.120	2.95	3.05	4
e	0.020 BSC		0.50 BSC		-
E	0.187	0.199	4.75	5.05	-
L	0.016	0.028	0.40	0.70	6
L1	0.037 REF		0.95 REF		-
N	10		10		7
R	0.003	-	0.07	-	-
R1	0.003	-	0.07	-	-
θ	5°	15°	5°	15°	-
α	0°	6°	0°	6°	-

Rev. 0 12/02

NOTES:

- These package dimensions are within allowable dimensions of JEDEC MO-187BA.
- Dimensioning and tolerancing per ANSI Y14.5M-1994.
- Dimension "D" does not include mold flash, protrusions or gate burrs and are measured at Datum Plane. Mold flash, protrusion and gate burrs shall not exceed 0.15mm (0.006 inch) per side.
- Dimension "E1" does not include interlead flash or protrusions and are measured at Datum Plane. **-H-** Interlead flash and protrusions shall not exceed 0.15mm (0.006 inch) per side.
- Formed leads shall be planar with respect to one another within 0.10mm (.004) at seating Plane.
- "L" is the length of terminal for soldering to a substrate.
- "N" is the number of terminal positions.
- Terminal numbers are shown for reference only.
- Dimension "b" does not include dambar protrusion. Allowable dambar protrusion shall be 0.08mm (0.003 inch) total in excess of "b" dimension at maximum material condition. Minimum space between protrusion and adjacent lead is 0.07mm (0.0027 inch).
- Datums **-A-** and **-B-** to be determined at Datum plane **-H-**.
- Controlling dimension: MILLIMETER. Converted inch dimensions are for reference only.

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